CM1263-02SE

Low Capacitance ESD Protection for High-Speed Serial Interfaces

ON Semiconductor®

http://onsemi.com

SOT−553
SE SUFFIX
CASE 463B

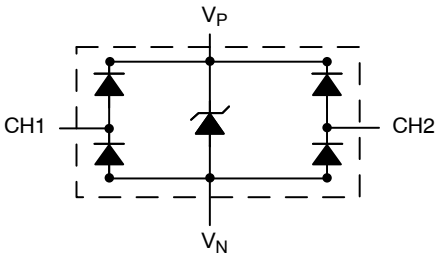
Features

- 2 Channels of ESD Protection
- 0.85 pF Loading Capacitance per Channel Typical
- Provides ESD Protection to IEC61000−4−2 Level 4:
  - ±8 kV Contact Discharge
  - ±15 kV Air Discharge
- 5−Pin SOT−553 Package
- These Devices are Pb−Free and are RoHS Compliant

Applications

- LCD and Camera Data Lines in Wireless Handsets that Use High−speed Serial Interfaces such as MDDI, MIPI, MVI and MPL
- I/O Port Protection for Mobile Handsets, Notebook Computers, PDAs, etc.
- Wireless Handsets
- Handheld PCs/PDAs
- LCD and Camera Modules

BLOCK DIAGRAM



MARKING DIAGRAM

L63 = Specific Device Code
M = Date Code

ORDERING INFORMATION

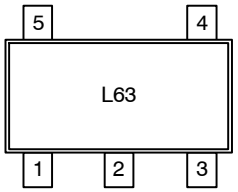
Device	Package	Shipping†
CM1263−02SE	SOT−553 (Pb−Free)	5000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Table 1. PIN DESCRIPTIONS

5−Pin, SOT−553 Package	
Pin	**Description**
1	V_P
2	V_N
3	NC
4	(CH1) ESD Channel #1
5	(CH2) ESD Channel #2

PACKAGE / PINOUT DIAGRAM



SPECIFICATIONS

Table 2. ABSOLUTE MAXIMUM RATINGS

Parameter	Rating	Units
Operating Supply Voltage ($V_P - V_N$)	6.0	V
Operating Temperature Range	−40 to +85	°C
Storage Temperature Range	−65 to +150	°C
DC Voltage at any channel input	(V_N − 0.5) to (V_P + 0.5)	V

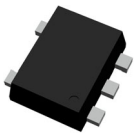
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Table 3. ELECTRICAL OPERATING CHARACTERISTICS (Note 1)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_P	Operating Supply Voltage ($V_P - V_N$)			3.3	5.5	V
I_P	Operating Supply Current	($V_P - V_N$) = 3.3 V			8.0	μA
V_F	Diode Forward Voltage Top Diode Bottom Diode	I_F = 8 mA; T_A = 25°C	 0.60 0.60	 0.80 0.80	 0.95 0.95	V
I_{LEAK}	Channel Leakage Current	T_A = 25°C; V_P = 5 V, V_N = 0 V, V_{TEST} = 0 to 5 V		0.1	1.0	μA
C_{IN}	Channel Input Capacitance	At 1 MHz, V_P = 3.3 V, V_N = 0 V, V_{IN} = 1.65 V		0.85	1.2	pF
ΔC_{IN}	Channel Input Capacitance Matching	At 1 MHz, V_P = 3.3 V, V_N = 0 V, V_{IN} = 1.65 V		0.02		pF
V_{ESD}	ESD Protection Peak Discharge Voltage at any channel input, in system: a) Contact Discharge per IEC 61000−4−2 standard b) Air Discharge per IEC 61000−4−2 standard	 T_A = 25°C; (Notes 2 and 3) T_A = 25°C; (Note 3)	 ±8 ±15			kV
V_{CL}	Channel Clamp Voltage Positive Transients Negative Transients	T_A = 25°C, I_{PP} = 1 A, t_P = 8/20 μS (Note 3)		 +9.96 −1.6		V
R_{DYN}	Dynamic Resistance Positive Transients Negative Transients	I_{PP} = 1 A, t_P = 8/20 μS Any I/O pin to Ground; (Note 3)		 0.96 0.5		Ω

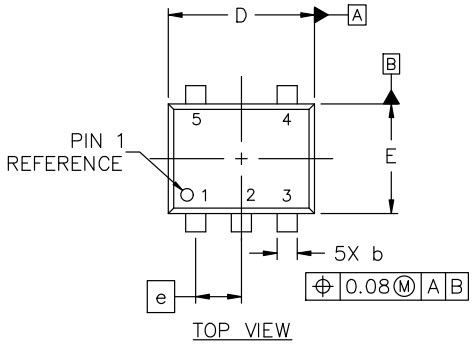
1. All parameters specified at T_A = −40°C to +85°C unless otherwise noted.
2. Standard IEC 61000−4−2 with $C_{Discharge}$ = 150pF, $R_{Discharge}$ = 330 Ω, V_P = 3.3 V, V_N grounded.
3. These measurements performed with no external capacitor on V_P (V_P floating).

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



SOT−553−5 1.60x1.20x0.55, 0.50P
CASE 463B
ISSUE D

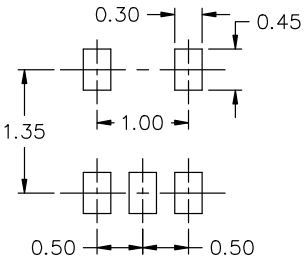
DATE 21 FEB 2024



NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.55	1.60	1.65
E	1.15	1.20	1.25
e	0.50 BSC		
H	1.55	1.60	1.65
L	0.10	0.20	0.30



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 2:
PIN 1. CATHODE
2. COMMON ANODE
3. CATHODE 2
4. CATHODE 3
5. CATHODE 4

STYLE 3:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. CATHODE 1

STYLE 4:
PIN 1. SOURCE 1
2. DRAIN 1/2
3. SOURCE 1
4. GATE 1
5. GATE 2

STYLE 5:
PIN 1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE

STYLE 6:
PIN 1. EMITTER 2
2. BASE 2
3. EMITTER 1
4. COLLECTOR 1
5. COLLECTOR 2/BASE 1

STYLE 7:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 8:
PIN 1. CATHODE
2. COLLECTOR
3. N/C
4. BASE
5. EMITTER

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. ANODE
5. ANODE

DOCUMENT NUMBER:	**98AON11127D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**SOT−553−5 1.60x1.20x0.55, 0.50P**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales